PCN	Number:	202302100	00.2A					PCN Date:		July 27, 2023		
Title	Qualific	cation of CDA	Tasa	as an alternate Assembly and test site for select devices								
Cus	tomer Cont	act:	Char	ige I	Management te	eam [	Dept		Qua	lity Services		
Pro	posed 1 <sup>st</sup> Sh	nip Date:	May	13,	2023			equests ed until:	Aug	27, 2023*		
*Sa	mple reque	sts received	after	· Au	g 27, 2023 wi	ll not be s	upp	orted, Re	ev A c	devices only		
Cha	nge Type:											
X	Assembly Si	te		Design				Wafer	Bump	Material		
X	Assembly Pr	ocess			Data Sheet	Data Sheet			Wafer Bump Process			
X	Assembly M	aterials			Part number	change		Wafer	Fab S	Site		
$\boxtimes$	Mechanical	Specification		$\boxtimes$	Test Site			Wafer	Fab I	Material		
	Packing/Shi	pping/Labeling			Test Process			Wafer	Fab I	Process		
	PCN Details											
Des	cription of (	Change:							•			

**Revision A** is to announce the <u>addition</u> of new devices that were not included on the original PCN notification. These new devices and some minor content changes are highlighted and **bolded** in the device list below. The expected first shipment date for these new devices will be 90 days from this notice for these newly added devices only.

Texas Instruments Incorporated is announcing the qualification of CDAT as an additional Assembly and test site for set of devices listed below. Construction differences are as follows:

What	UTL1	CDAT
Mount Compound	SID#PZ0035	4207123
Lead Finish	Matte Sn	NiPdAu
Bond wire composition, diameter***	Cu, 1.3 mil	Cu, 1.0 mil
MSL **	Level 1	Level 2
Bond wire composition, diameter****	Au, 1.3 mil	Cu, 0.96 mil

#### \*\* - DRB Devices only

\*\*\* - NGU devices only

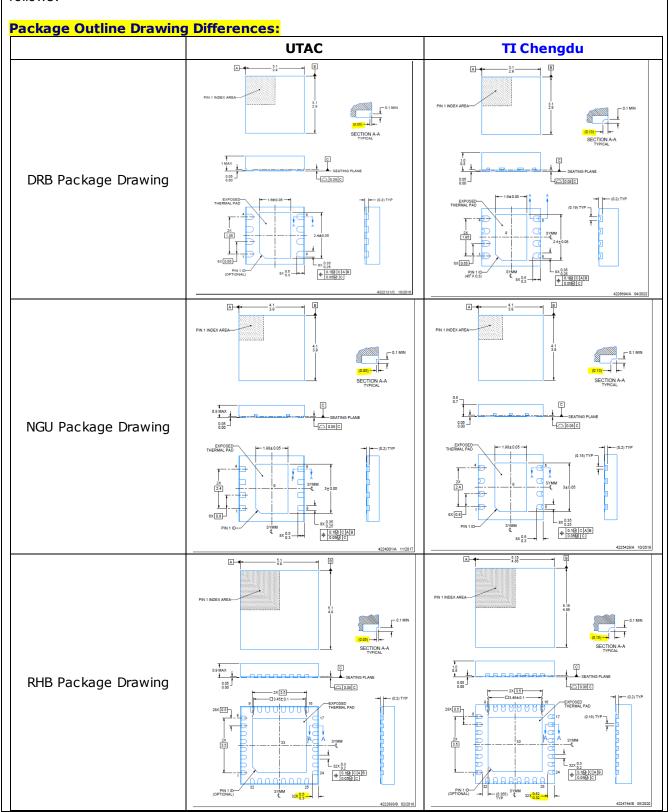
\*\*\*\* - TUSB217xRGYx devices only

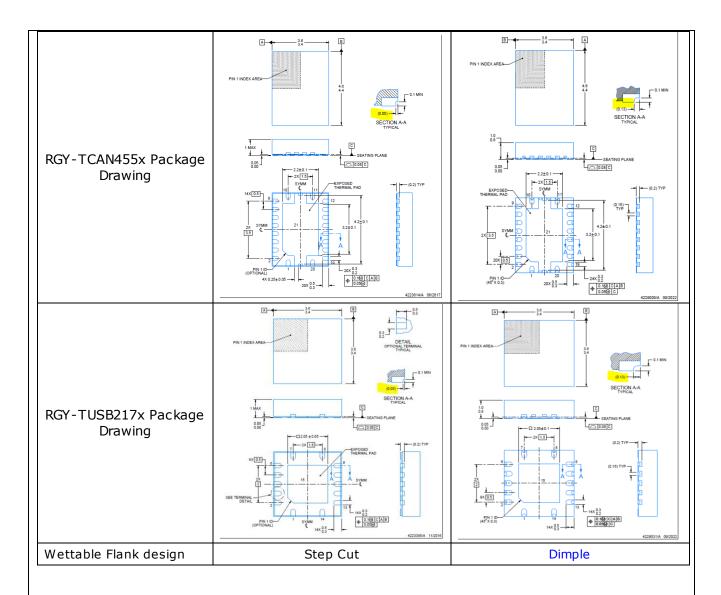
#### **Marking Differences:**

	UTAC	TI Chengdu
RHB Package	UTAC  ! O	1

ECAT	G3	G4	

With the advent of CDAT Assembly, there will be minor package outline dimension differences as follows:





Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ

Upon expiry of this PCN, there will be a transition period where TI will combine lead free solutions in a single <u>standard part number</u> For example; <u>TCAN4550RGYRQ1</u> – can ship with both Matte Sn and NiPdAu.

#### Example:

- Customer order for 7500 units of TCAN4550RGYRQ1 with 2500 units SPQ (Standard Pack Quantity per Reel).
- TI can satisfy the above order in one of the following ways.
  - I. 3 Reels of NiPdAu finish.
  - II. 3 Reels of Matte Sn finish
  - III. 2 Reels of Matte Sn and 1 reel of NiPdAu finish.
  - IV. 2 Reels of NiPdAu and 1 reel of Matte Sn finish.

## **Reason for Change:**

Supply continuity

## Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

#### **Impact on Environmental Ratings**

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☑ No Change	No Change     ■     No Change     ■     No Change     No Change     ■     No Change     ■     No Change     No Change		No Change     ■     No Change     N

#### Changes to product identification resulting from this PCN:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
UTL1	NSE	THA	Bangkok
CDAT	CDA	CHN	Chengdu

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 2Q: MSL 2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT: ITEM:

TTEM: 5A (L)TO:1750

(a) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483S12 G3 = Matte Sn

G4 = NiPdAu

(2P) REV: (V) 0033317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

**Product Affected:** 

LM25180QNGURQ1	LP87702TRHBRQ1	TCAN1042HGVDRBTQ1	TCAN1051HDRBTQ1
LM5180QNGURQ1	LP87702TRHBTQ1	TCAN1042HVDRBRQ1	TCAN1051HGDRBRQ1
LM5180QNGUTQ1	TCAN1042DRBRQ1	TCAN1042HVDRBTQ1	TCAN1051HGDRBTQ1
LM5181QNGURQ1	TCAN1042DRBTQ1	TCAN1042VDRBRQ1	TCAN1051HGVDRBRQ1
LP877020RHBRQ1	TCAN1042GDRBRQ1	TCAN1042VDRBTQ1	TCAN1051HGVDRBTQ1
LP87702DRHBRQ1	TCAN1042GDRBTQ1	TCAN1051DRBRQ1	TCAN1051HVDRBRQ1
LP87702DRHBTQ1	TCAN1042GVDRBRQ1	TCAN1051DRBTQ1	TCAN1051HVDRBTQ1
LP87702KRHBRQ1	TCAN1042GVDRBTQ1	TCAN1051GDRBRQ1	TCAN1051VDRBRQ1
LP87702KRHBTQ1	TCAN1042HDRBRQ1	TCAN1051GDRBTQ1	TCAN1051VDRBTQ1
LP87702PRHBRQ1	TCAN1042HDRBTQ1	TCAN1051GVDRBRQ1	TCAN4550RGYRQ1
LP87702PRHBTQ1	TCAN1042HGDRBRQ1	TCAN1051GVDRBTQ1	TCAN4550RGYTQ1
LP87702RRHBRQ1	TCAN1042HGDRBTQ1	TCAN1051HDRBRQ1	TCAN4551RGYRQ1
LP87702RRHBTQ1	TCAN1042HGVDRBRQ1	TUSB217RGYRQ1	TUSB217RGYTQ1

#### Approve Date 18-JANUARY -2023

#### Product Attributes

Attributes	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:	QBS Reference:	QBS Reference:
Attributes	TCAN4550RGYRQ1	TLC6C5816QPWPRQ1	TLIN10283DRBRQ1	TLIN10285DRBRQ1	TLIN2024RGYRQ1	TCAN11625DMTRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Power Management	Interface	Interface	Interface	Interface
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	RFAB, RFAB	RFAB
Assembly Site	CDAT	TAI	CDAT	CDAT	CDAT	CDAT
Package Group	QFN	TSSOP	QFN	QFN	QFN	QFN
Package Designator	RGY	PWP	DRB	DRB	RGY	DMT
Pin Count	20	28	8	8	24	14

- QBS: Qual By Similarity
   Qual Device TCAN4550RGYRQ1 is qualified at MSL2 260C

#### Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: TCAN4550RGYRQ1	QBS Reference: TLC6C5816QPWPRQ1	QBS Reference: TLIN10283DRBRQ1	QBS Reference: TLIN10285DRBRQ1	QBS Reference: TLIN2024RGYRQ1	QBS Reference: TCAN11625DMTRQ1
Test Group	Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	QBS (1)	-	Pass	Pass	Pass	-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	QBS (1)	-	1/77/0	2/154/0	3/231/0	-
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	QBS (1)	-	1/77/0	2/154/0	3/231/0	-

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ICAN4550RGYRQ1	QBS Reference: TLC6C5816QPWPRQ1	QBS Reference: TLIN10283DRBRQ1	QBS Reference: TLIN10285DRBRQ1	QBS Reference: TLIN2024RGYRQ1	QBS Reference: TCAN11625DMTRQ1
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	1000 Cycles	QBS (1)	-	-	1/77/0	-	
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	QBS (1)	-	1/77/0	1/77/0	3/231/0	-
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	QBS (1)	-	-	-	1/5/0	-
PTC	A5	JEDEC JESD22- A105	1	45	PTC	-40/125C	1000 Cycles	N/A	-	-	1/45/0	1/45/0	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	QBS (1)	-	1/77/0	2/154/0	2/90/0	-
Test Group	B - Acce	lerated Lifetime	e Simula	ition Tes	ts								
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	QBS (2)	3/231/0	-	-	-	3/231/0
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	150C	1000 Hours	QBS (2)	-	1/77/0	2/154/0	-	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	QBS (2)	3/2400/0				
Test Group	C - Pack	age Assembly	Integrity	Tests									
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	1/30/0	2/60/0	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	1/30/0	2/60/0	3/90/0	-
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	1/15/0	1/15/0	-
SD	СЗ	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage		-	-	-	1/15/0	1/15/0	-
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	-	-	-	3/30/0	-
Test Group	D - Die F	abrication Relia	ability Te	sts									
ЕМ	D1	JESD61		-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: TCAN4550RGYRQ1	QBS Reference: TLC6C5816QPWPRQ1	QBS Reference: TLIN10283DRBRQ1	QBS Reference: TLIN10285DRBRQ1	QBS Reference: TLIN2024RGYRQ1	QBS Reference: ICAN11625DMTRQ1
TDDB	D2	JESD35			Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-			Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E	- Electr	ical Verification	Tests										
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0		-	-	-	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
  The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/Ik Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
  The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/Ik Hours, and 170C/420 Hours
  The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 1 (or E): -40C to +150C
  Grade 1 (or Q): -40C to +125C
  Grade 2 (or T): -40C to +105C
  Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold: HTOL, ED
   Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
   Room: AC/uHAST

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

QBS (1) - Package QBS to TLIN2024RGYRQ1, TLIN10285DRBRQ1, TLIN10283DRBRQ1 with same package attributes. TLIN10285DRBRQ1 /TLIN10283DRBRQ1 has been Q006 tested.

QBS (2) - Process QBS to TLC6C5816QPWPRQ1 and TCAN11625DMTRQ1 with same silicon attributes

## **Rev A Device qual Memos:**

# Automotive Change Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

#### Approve Date 02-June-2023

#### Product Attributes

Attributes	Qual Device: TCAN1042HGVDRBRQ1	Qual Device: TCAN1042HGVDRBRQ1	Process QBS Reference: TCAN1042HVDRQ1	Process QBS Reference: TCAN1051VDRQ1	Process QBS Reference: TCAN1042HVDRQ1	Package QBS Reference: CAXC8T245QRHLRQ1_	Package QBS Reference: TLIN10283DRBRQ1	QBS Reference: TLIN10285DRBRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Interface	Interface	Interface	Logic	Interface	Interface
Wafer Fab Supplier	MH8	MAINEFAB	MH8	MH8	MAINEFAB	MH8	RFAB	RFAB
Assembly Site	CDAT	CDAT	FMX	FMX	FMX	CDAT	CDAT	CDAT
Package Group	QFN	QFN	SOIC	SOIC	SOIC	QFN	QFN	QFN
Package Designator	DRB	DRB	D	D	D	RHL	DRB	DRB
Pin Count	8	8	8	8	8	24	8	8

- QBS: Qual By Similarity
   Qual Device TCAN1042HGVDRBRQ1 is qualified at MSL2 260C

#### Qualification Results

Туре	*	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ICAN1042HGVDRBRQ1	Qual Device: TCAN1042HGVDRBRQ1	Process QBS Reference: TCAN1042HVDRQ1	Process QBS Reference: TCAN1051VDRQ1	Process QBS Reference: TCAN1042HVDRQ1	Package QBS Reference: CAXC8T245QRHLRQ1_	Package QBS Reference: TUN10283DRBRQ1	Package QBS Reference: TLIN10285DRBRQ1
Test Group	est Group A - Accelerated Environment Stress Tests														
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step		-		-	-	3/Pass		
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	1 Step	QBS (1)	QBS (1)			-		1/Pass	2/Pass
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	QBS (1)	QBS (1)	-		-	3/231/0	1/77/0	2/154/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	QBS (1)	QBS (1)		-	-	3/231/0	1/77/0	2/154/0

Туре	*	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TCAN1042HGVDRBRQ1	Qual Device: TCAN1042HGVDRBRQ1	Process QBS Reference: ICAN1042HVDRQ1	Process QBS Reference: ICAN1051VDRQ1	Process QBS Reference: ICAN1042HVDRQ1	Package QBS Reference: CAXC8T245QRHLRQ1	Package QBS Reference: TUN10283DRBRQ1	Package QBS Reference: ILIN10285DRBRQ1
тс	Α4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	1000 Cycles	QBS (1)	QBS (1)			-			1/77/0
тс	Α4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	QBS (1)	QBS (1)			-	3/231/0	1/77/0	1/77/0
PTC	A5	JEDEC JESD22- A105	1	45	PTC	-40/125C	1000 Cycles	-	-	-	-	-	-	-	1/45/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	QBS (1)	QBS (1)	-	-	-	3/135/0	1/77/0	2/154/0
Test Group	B - Accele	erated Lifetime	Simulation	n Tests											
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours				-		3/231/0		
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	150C	1000 Hours	QBS (1)	QBS (1)		-	-	-	1/77/0	2/154/0
HTOL	81	JEDEC JESD22- A108	1	77	Life Test	150C	300 Hours	QBS (2)	QBS (2)	2/154/11	1/77/0	3/231/0	-	-	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	QBS (2)	QBS (2)	2/1600/0	1/800/0	3/2400/0	-	-	-
EDR	B3	AEC Q100- 005	1	77	NVM Endurance, Data Retention, and Op Life	Per QSS- 009-018	1 Step	-			-	-	-	1/77/0	2/154/0
Test Group	C - Packa	ge Assembly In	tegrity Te	sts											
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpl>1.67	Wires	1/30/0	1/30/0		-		3/90/0	-	
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpl>1.67	Wires	1/30/0	1/30/0	-	-	-	3/90/0	-	
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage		QBS (1)	QBS (1)	-	-	-	-	-	1/15/0
SD	C3	JEDEC J. STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	QBS (1)	QBS (1)	-	-	-	-	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cplo1.67	-	1/10/0	1/10/0	-	-	-		1/10/0	2/20/0
Test Group	D - Die Fal	brication Reliab	ility Test												
ЕМ	D1	JESD61	-	-	Electromigration			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35			Time Dependent Dielectric Breakdown		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
на	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Туре	#	Test Spec	Min Lot	SS/	Test Name	Condition	Duration	Qual Device: TCAN1042HGVDRBRQ1	Qual Device: TCAN1042HGVDRBRQ1	Process QBS Reference:	Process QBS Reference:	Process QBS Reference:	Package QBS Reference:	Package QBS Reference:	Package QBS Reference:
		шиорсо	Qby	Lot				TCANI042HGVDRBRQ1  Completed Per Process	TCANI042HGVDRBRQ1  Completed Per Process	TCAN1042HVDRQ1  Completed Per	TCAN10S1VDRQ1	TCAN1042HVDRQ1  Completed Per	CAXC8T245QRHLRQ1	TUNI028SDRBRQ1  Completed Per	TLIN10285DRBRQ1
SM	D5	-	-	-	Stress Migration	-	-	Technology Requirements	Technology Requirements	Process Technology Requirements	Process Technology Requirements	Process Technology Requirements	Completed Per Process Technology Requirements	Process Technology Requirements	Process Technology Requirements
Test Group	E - Electri	cal Verification	Tests												
ED	E6	AEC Q100- 009	3	30	Electrical Distributions	Cpl>1.67 Room, hot, and cold	-	1/30/0		-		-	-	-	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Blased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
  The following are equivalent HTOL options based on an activation energy of 0.7 eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
  The following are equivalent HTSL options based on an activation energy of 0.7 eV: 150C/1k Hours, and 170C/420 Hours
  The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): .40C to +150C
   Grade 1 (or Q): -40C to +125C
   Grade 2 (or T): .40C to +105C
   Grade 3 (or I): .40C to +85C

- E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
- Room/Hot/Cold: HTOL, ED
   Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
   Room: AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2209-031

QBS (1) - Package QBS to TLIN10283DRBRQ1/TLIN10285DRBRQ1 with same package attributes. Q006 QBS to CAXC8T245QRHLRQ1.

QBS (2) - MH8/MFAB ABCD05HV Process QBS to TCAN1042VDRQ1/TCAN1051VDQ1/TCAN1042HVDRQ1 with same silicon attributes

[1]- 1 EOS fail Discounted, QEM-EVAL-1801-00348 8D reports EOS damage to be caused by mishandling of units during the cold temperature electrical test insertion.

## Approve Date 05-June-2023

#### **Product Attributes**

Attributes	Qual Device:	QBS Reference:	QBS Reference:
Attibutes	LM5180QNGURQ1	UCC27282QDRCRQ1	PDRV8889QWRGERQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Power Management
Wafer Fab Supplier	MAINEFAB	MAINEFAB	RFAB
Assembly Site	CDAT	CDAT	CDAT
Package Group	QFN	QFN	QFN
Package Designator	NGU	DRC	RGE
Pin Count	8	10	24

- QBS: Qual By Similarity
- Qual Device LM5180QNGURQ1 is qualified at MSL2 260C

#### **Qualification Results**

Туре	Qty Lut		Test Name	Condition	Duration	Qual Device: LM5180QNGURQ1	QBS Reference: UCC27282QDRCRQ1	QBS Reference: PDRV8889QWRGERQ1		
Test Group	A - Acce	lerated Environ	nment St	ress Tes	sts					
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	1/PASS	3/PASS	3/PASS
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	QBS (1)	3/231/0	3/231/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	QBS (1)	-	3/231/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	QBS (1)	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0		-
PTC	A5	JEDEC JESD22- A105	1	45	PTC	-40/125C	1000 Cycles	-	-	1/45/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	QBS (1)	3/135/0	3/231/0
Test Group	B - Acce	lerated Lifetime	e Simula	tion Test	ts					
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	QBS (2)	3/231/0	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	QBS (2)	3/2400/0	-

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LM5180QNGURQ1	QBS Reference: UCC27282QDRCRQ1	QBS Reference: PDRV8889QWRGERQ1
Test Group	A - Acce	elerated Environ	ment Si	ress Te	sts					
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	1/PASS	3/PASS	3/PASS
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	QBS (1)	3/231/0	3/231/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	QBS (1)	-	3/231/0
AC/UHAST	АЗ	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	QBS (1)	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-	-
РТС	A5	JEDEC JESD22- A105	1	45	PTC	-40/125C	1000 Cycles	-	-	1/45/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	QBS (1)	3/135/0	3/231/0
Test Group	B - Acce	elerated Lifetime	e Simula	tion Tes	ts					
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	QBS (2)	3/231/0	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	QBS (2)	3/2400/0	-

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LM5180QNGURQ1	QBS Reference: UCC27282QDRCRQ1	QBS Reference: PDRV8889QWRGERQ1
Test Group	C - Pack	age Assembly	Integrity	Tests	<u> </u>					
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/15/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/15/0	3/90/0
SD	C3	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	QBS (1)	3/90/0	-
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	3/30/0
Test Group	D - Die F	abrication Relia	ability Te	sts						
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LM5180QNGURQ1	QBS Reference: UCC27282QDRCRQ1	QBS Reference: PDRV8889QWRGERQ
Test Group	E - Elect	rical Verification	n Tests							
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	-	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- $\bullet \quad \text{The following are equivalent HTSL options based on an activation energy of 0.7eV: } 150\text{C/1k Hours, and } 170\text{C/420 Hours}$
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

• Grade 0 (or E): -40C to +150C

Additional Tests

- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2209-084

QBS (1) - Package QBS to UCC27282QDRCRQ1, PDRV8889QWRGERQ1 with same package attributes. PDRV8889QWRGERQ1 has been Q006 tested.

QBS (2) - Process QBS to UCC27282QDRCRQ1 with same silicon attributes



#### DRV8889WRGEQ1 - RFAB/CD-PR/CDAT - Grade 1 Q100 Rev H Q006 Approved 06-Dec-2019

#### **Product Attributes**

Attributes	Qual Device: DRV8889WRGEQ1	Qual Device: DRV8889WRGEQ1-1P1	Qual Device: DRV8889WRGEQ1-1P2
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +125 C
Product Function	Power Management	Power Management	Power Management
Wafer Fab Supplier	RFAB	RFAB	RFAB
Assembly Site	CDAT	CDAT	CDAT
Package Type	VQFN	VQFN	VQFN
Package Designator	RGE (4 X 4 QFN)	RGE (4 X 4 QFN)	RGE (4 X 4 QFN)
Ball/Lead Count	24	24	24

<sup>-</sup> QBS: Qual By Similarity

## Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec Test Group A – A	Min Lot Qty ccelera	SS/Lot	Test Name / Condition	Duration	Qual Device: DRV8889WRGEQ1	Qual Device: DRV8889WRGEQ1- 1P1	Qual Device: DRV8889WRGEQ1- 1P2
Г	PC	A1	-	3	22	SAM Analysis, Pre Stress	Completed	2/44/0	1/22/0	-
Г	PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 3- 260C	No fails	No fails	-
	PC	A1	-	3	22	SAM Analysis, Post Stress	Completed	2/44/0	1/22/0	-
Г	HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	2/154/0	1/77/0	-

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: DRV8889WRGEQ1	Qual Device: DRV8889WRGEQ1- 1P1	Qual Device: DRV8889WRGEQ1- 1P2
HAST	A2	-	3	1	Cross Section, Post bHAST 96 Hours	Completed	2/2/0	1/1/0	-
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 96 Hours	Wires	2/60/0	1/30/0	-
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	2/60/0	1/30/0	-
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	2/60/0	1/30/0	-
HAST	A2	JEDEC JESD22-A110	3	70	Biased HAST, 130C/85%RH	192 Hours	3/210/0	3/210/0	-
HAST	A2	-	3	1	Cross Section, Post bHAST 192 Hours	Completed	2/2/0	1/1/0	-
HAST	A2	-	3	22	SAM Analysis, Post bHAST, 192 Hours	Completed	2/44/0	1/22/0	-
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 192 Hours	Wires	2/60/0	1/30/0	-
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	2/60/0	1/30/0	-
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	2/60/0	1/30/0	-
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	2/154/0	1/77/0	-
тс	A4	-	3	1	Cross Section, Post T/C 500 Cycles	Completed	2/2/0	1/1/0	-
тс	A4	-	3	22	SAM Analysis, Post T/C, 500 Cycles	Completed	2/44/0	1/22/0	-
тс	A4	-	3	30	Wire Bond Shear, Post T/C 500 Cycles	Wires	2/60/0	1/30/0	•
тс	A4	-	3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	2/60/0	1/30/0	-
тс	A4	-	3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	2/60/0	1/30/0	-
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle, -65/150C	1000 Cycles	2/140/0	1/70/0	-
тс	A4	-	3	1	Cross Section, Post T/C 1000 Cycles	Completed	2/2/0	1/1/0	-
тс	A4	-	3	22	SAM Analysis, Post T/C, 1000 Cycles	Completed	2/44/0	1/22/0	-
TC	A4	-	3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	2/60/0	1/30/0	-
тс	A4	-	3	30	Bond Pull over Stitch, Post T/C, 1000 Cycles	Wires	2/60/0	1/30/0	-

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: DRV8889WRGEQ1	Qual Device: DRV8889WRGEQ1- 1P1	Qual Device: DRV8889WRGEQ1- 1P2
TC	A4	-	3	30	Bond Pull over Ball, Post T/C, 1000 Cycles	Wires	2/60/0	1/30/0	-
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle - 40/125C	1000 Cycles	-	-	-
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle - 40/125C	2000 Cycles	-	-	-
HTSL	A6	JEDEC JESD22-A103	3	45	High Temp Storage Bake 150C	1000 Hours	2/90/0	1/45/0	-
HTSL	A6	-	3	1	Cross Section, Post HTSL 1000 Hours	Completed	2/2/0	1/1/0	-
HTSL	A6	JEDEC JESD22-A103	3	44	High Temp Storage Bake 150C	2000 Hours	2/88/0	1/44/0	-
HTSL	A6	-	3	1	Cross Section, Post HTSL 2000 Hours	Completed	2/2/0	1/1/0	-
		Test Group C –	Packag	je Assemi	bly Integrity Tests				
WBS	C1	AEC Q100-001	3	30	Wire Bond Shear, Cok>1.67	Wires	1/30/0	1/30/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	3	30	Bond Pull over Ball, Cok >1.67	Wires	1/30/0	1/30/0	1/30/0

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST & TC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

# E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20180731-126552

#### Approve Date 09-June-2023 Product Attributes

Attributes	Qual Device:	Process, Package QBS Reference:	Package Reference:
Attributes	LP87702DRHBRQ1	LM2775QDSGRQ1	TPS92682QRHBRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Power Management
Wafer Fab Supplier	DMOS6	RFAB	RFAB
Assembly Site	CDAT	CDAT	CDAT
Package Group	QFN	QFN	QFN
Package Designator	RHB	DSG	RHB
Pin Count	32	8	32

- QBS: Qual By Similarity
- Qual Device LP87702DRHBRQ1 is qualified at MSL2 260C

#### **Qualification Results**

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LP87702DRHBRQ1	Process, Package QBS Reference: <u>LM2775QDSGRQ1</u>	Package QBS Reference: <u>TPS92682QRHBRQ1</u>
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Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LP87702DRHBRQ1	Process, Package QBS Reference: LM2775QDSGRQ1	Package QBS Reference: <u>TPS92682QRHBRQ1</u>
Test Group	A - Acce	lerated Environme	ent Stres	s Tests						
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	QBS(1)	3/PASS	-
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL3 260C	-	-	-	3/PASS
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	QBS(1)	3/231/0	3/231/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	QBS(1)	3/231/0	3/231/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	QBS(1)	3/231/0	3/231/0
PTC	A5	JEDEC JESD22-A105	1	45	PTC	-40/125C	1000 Cycles	-	1/45/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	QBS(1)	-	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	QBS(1)	3/135/0	-
Test Group	B - Acce	lerated Lifetime S	imulatio	n Tests						
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	QBS(2)	3/231/0	-
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	150C	324 Hours	-	-	1/77/0
Test Group	C - Pack	age Assembly Inte	egrity Te	sts						
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LP87702DRHBRQ1	Process, Package QBS Reference: LM2775QDSGRQ1	Package QBS Reference: <u>TPS92682QRHBRQ1</u>		
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0		
SD	СЗ	JEDEC J-STD- 002	1	15	PB Solderability	>95% Lead Coverage	-	QBS(1)	1/15/0	3/44/0		
SD	СЗ	JEDEC J-STD- 002	1	15	PB-Free Solderability	>95% Lead Coverage	-	QBS(1)	1/15/0	3/44/0		
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	-	3/30/0		
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements		
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements		
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements		
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements		
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements		
Test Group	E - Elect	rical Verification To	ests									
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	-	-		
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LP87702DRHBRQ1	Process, Package QBS Reference: LM2775QDSGRQ1	Package QBS Reference: <u>TPS92682QRHBRQ1</u>		
Additional T	ests											

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2209-077

QBS (1) - Package QBS to LM2775QDSGRQ1 and TPS92682QRHB with same package attributes. LM2775QDSGRQ1 and TPS92682QRHB have been Q006 tested.

QBS (2) - Process QBS to LM2775QDSGRQ1 with same silicon attributes

#### Approve Date 14-July-2023

#### **Product Attributes**

Attributes	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:	QBS Reference:	
Attributes	TUSB217RGYRQ1	TLC6C5816QPWPRQ1	TS3A5017QRGYRQ1	TLIN10283DRBRQ1	TLIN10285DRBRQ1	
Automotive Grade Level	Grade 2	Grade 1	Grade 1	Grade 1	Grade 1	
Operating Temp Range (C)	-40 to 105	-40 to 125	-40 to 125	-40 to 125	-40 to 125	
Product Function	Signal Chain	Power Management	Signal Chain	Interface	Interface	
Wafer Fab Supplier	RFAB	RFAB	FR-BIP-1	RFAB	RFAB	
Assembly Site	CDAT	TAI	CDAT	CDAT	CDAT	
Package Group	QFN	TSSOP	QFN	QFN	QFN	
Package Designator	RGY	PWP	RGY	DRB	DRB	
Pin Count	14	28	16	8	8	

- QBS: Qual By Similarity
   Qual Device TUSB217RGYRQ1 is qualified at MSL2 260C

#### **Qualification Results**

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TUSB217RGYRQ1	Process QBS Reference: TLC6C5816QPWPRQ1	QBS Reference: TS3A5017QRGYRQ1	QBS Reference: TLIN10283DRBRQ1	QBS Reference: TLIN10285DRBRQ1
Test Group	A - Acce	lerated Environ	ment St	ress Tes	sts							
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C		QBS(1)	-	3/Pass	1/Pass	2/Pass
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	QBS(1)		3/231/0	1/77/0	2/154/0

Туре		Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TUSB217RGYRQ1	Process QBS Reference: TLC6C5816QPWPRQ1	QBS Reference: TS3A5017QRGYRQ1	QBS Reference: TLIN10283DRBRQ1	QBS Reference: TLIN10285DRBRQ1	
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	QBS(1)		3/231/0	1/77/0	2/154/0	
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	QBS(1)		3/231/0	2/154/0		
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	1000 Cycles	QBS(1)				1/77/0	
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	QBS(1)	-	1/5/0	1/5/0	1/5/0	
PTC	A5	JEDEC JESD22- A105	1	45	PTC	-40/125C	1000 Cycles				-	1/45/0	
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	QBS(1)		3/135/0	1/77/0	2/154/0	
To ad Onesia I	Fest Group B - Accelerated Lifetime Simulation Tests												
rest Group i	D - ACCE	Herateu Liietiiii	e Simula	mon les	ıs								
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	QBS(2)	3/231/0	3/231/0			
		JEDEC JESD22-				125C		QBS(2)	3/231/0	3/231/0	1/77/0	2/154/0	
HTOL	B1	JEDEC JESD22- A108 JEDEC JESD22-	1	77	Life Test		Hours 1000						
HTOL	B1	JEDEC JESD22- A108 JEDEC JESD22- A108 AEC Q100-	1	77	Life Test Life Test Early Life	150C	Hours 1000 Hours	QBS(2)	-	-	1/77/0	2/154/0	
HTOL HTOL ELFR EDR	B1 B1 B2 B3	JEDEC JESD22- A108 JEDEC JESD22- A108 AEC Q100- 008	1 1 1	77 77 77	Life Test  Life Test  Early Life Failure Rate  NVM Endurance, Data Retention,	150C 125C Per QSS-009-	1000 Hours 48 Hours	QBS(2)	3/2400/0		1/77/0	2/154/0	
HTOL HTOL ELFR EDR	B1 B1 B2 B3	JEDEC JESD22- A108 JEDEC JESD22- A108 AEC Q100- 008 AEC Q100- 005	1 1 1	77 77 77	Life Test  Life Test  Early Life Failure Rate  NVM Endurance, Data Retention,	150C 125C Per QSS-009-	1000 Hours 48 Hours	QBS(2)	3/2400/0		1/77/0	2/154/0	
HTOL HTOL ELFR EDR Test Group	B1 B2 B3 C - Pack	JEDEC JESD22- A108  JEDEC JESD22- A108  AEC Q100- 008  AEC Q100- 005  AEC Q100- AEC Q100-	1 1 1 Integrity	77 77 77 77 Tests	Life Test  Life Test  Early Life Failure Rate  NVM Endurance, Data Retention, and Op Life  Wire Bond	150C  125C  Per QSS-009-018  Minimum of 5 devices, 30 wires	1000 Hours 48 Hours 1 Step	QBS(2)  QBS(2)	3/2400/0		1/77/0	2/154/0	

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TUSB217RGYRQ1	Process QBS Reference: TLC6C5816QPWPRQ1	QBS Reference: TS3A5017QRGYRQ1	QBS Reference: TLIN10283DRBRQ1	QBS Reference: TLIN10285DRBRQ1	
SD	СЗ	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage		-	1/15/0	1/15/0		1/15/0	
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	3/30/0	1/10/0	2/20/0	
Test Group	Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
TDDB	D2	JESD35			Time Dependent Dielectric Breakdown		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
NBTI	D4	-			Negative Bias Temperature Instability			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
SM	D5	-	-		Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	
Test Group	E - Elect	rical Verificatio	n Tests										
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold		1/30/0			-		
Additional 1	Tests											ı	

#### Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
  The following are equivalent HTSL options based on an activation energy of 0.7eV: 125C/1k Hours, and 170C/420 Hours
  The following are equivalent Temp Cycle options per JESD47:-55C/125C/700 Cycles and -65C/150C/500 Cycles

#### Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
   Grade 1 (or Q): -40C to +125C
- Grade 3 (or I) : -40C to +85C
- E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
- Room/Hot/Cold: HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

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TI Qualification ID: R-CHG-2209-079

QBS (1) - Package QBS to TS3A5017QRGYRQ1, TLIN10285DRBRQ1, TLIN10285DRBRQ1 with same package attributes. TLIN10285DRBRQ1 / TLIN10285DRBRQ1 has been Q006 tested.

QBS (2) - Process QBS to TLC6C5816QPWPRQ1 with same silicon attributes

#### Approve Date 18-JANUARY -2023 Product Attributes

TLIN10283DRBRQ1	TLIN10285DRBRQ1
Die Attributes	
RFAB	RFAB
LBC9M	LBC9M
1650 x 1830	1650 x 1830
Package Attributes	
CDAT	CDAT
QFN	QFN
DRB	DRB

#### Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	TLIN10283DRBRQ1	TLIN10285DRBRQ1
Test G	roup A - /	Accelerated Environment S	tress Test	s					<u> </u>
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	1/Pass	2/Pass
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	1/22/0	2/44/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	1/22/0	2/44/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	2/154/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	1/30/0	2/60/0
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	1/30/0	2/60/0
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	1/30/0	2/60/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	1/70/0	2/140/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	1/22/0	2/44/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	1/1/0	2/1/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	1/30/0	2/60/0
HAST	A2.2.4		3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	1/30/0	2/60/0

HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	1/30/0	2/60/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	1000 Cycles	-	1/77/0
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	1/22/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-
тс	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-	1/30/0
тс	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires		1/30/0
тс	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires		1/30/0
тс	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-55C/150C	2000 Cycles	-	1/70/0
тс	A4.1.1	-	3	22	SAM Analysis, post TC 2X	Review for delamination	Completed	-	1/22/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	-
тс	A4.1.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	-	1/30/0
тс	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires		1/30/0
тс	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires		1/30/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	1/77/0
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	1/22/0	1/22/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-
тс	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	1/30/0	1/30/0

TC	A4.1.4		3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	1/30/0	1/30/0
TC	A4.1.5	120	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	1/30/0	1/30/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	1/70/0	1/70/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	1/22/0	1/22/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	1/1/0	1/1/0
TC	A4.2.3		3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	1/30/0	1/30/0
TC	A4.2.4		3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	1/30/0	1/30/0
тс	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	1/30/0	1/30/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	1/45/0	2/90/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL,	Post stress cross section	Completed	-	-
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	1/44/0	2/88/0
HTSL	A6.2.1		3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	1/1/0	2/2/0

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- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

#### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
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TI Qualification ID: 20200329-133554

Affected ZVEI IDs: SEM-PA-05, SEM-PA-07, SEM-PA-18, SEM-TF-01, SEM-PA-01, SEM-PA-08, SEM-PA-13, SEM-PS-02

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